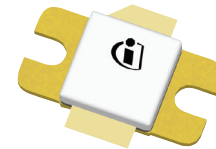


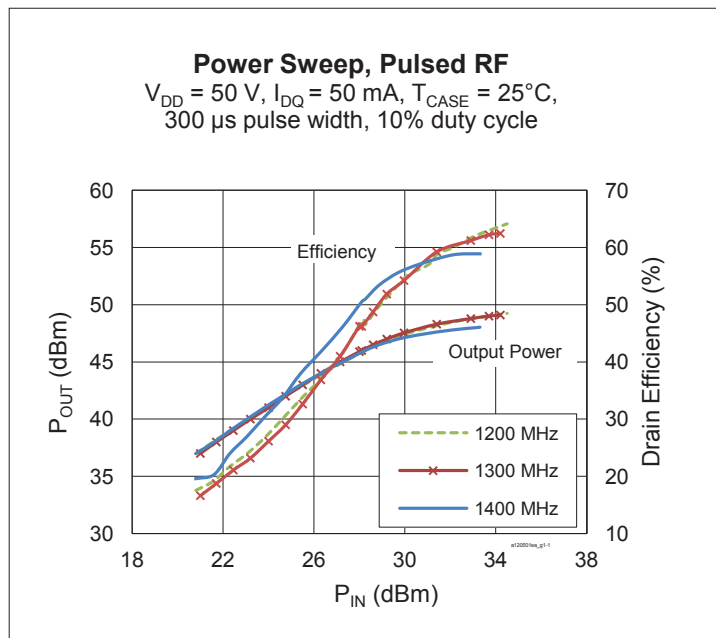
## Thermally-Enhanced High Power RF LDMOS FET 50 W, 50 V, 1200 – 1400 MHz

### Description

The PTVA120501EA LDMOS FET is designed for use in power amplifier applications in the 1200 to 1400 MHz frequency band. Features include high gain and thermally-enhanced package with bolt-down flange. Manufactured with Infineon's advanced LDMOS process, this device provides excellent thermal performance and superior reliability.



PTVA120501EA  
Package H-36265-2



### Features

- Broadband input matching
- High gain and efficiency
- Typical Pulsed CW performance, 1200 – 1400MHz, 50 V, 300  $\mu\text{s}$  pulse width, 10 % duty cycle, class AB
  - Output power at  $P_{1dB} = 54\text{ W}$
  - Efficiency = 55%
  - Gain = 16 dB
- Integrated ESD protection
- Low thermal resistance
- Pb-free and RoHS compliant
- Capable of withstanding a 10:1 load mismatch (all phase angles) at 50 W peak under RF pulse, 300  $\mu\text{s}$ , 10% duty cycle.

### RF Characteristics

#### Pulsed RF Performance (tested in Infineon test fixture)

$V_{DD} = 50\text{ V}$ ,  $I_{DQ} = 50\text{ mA}$ ,  $P_{OUT} = 50\text{ W}$ ,  $f_1 = 1200\text{ MHz}$ ,  $f_2 = 1300\text{ MHz}$ ,  $f_3 = 1400\text{ MHz}$ , 300  $\mu\text{s}$  pulse width, 10 % duty cycle

Characteristic	Symbol	Min	Typ	Max	Unit
Gain	$G_{ps}$	16.5	17	—	dB
Drain Efficiency	$\eta_D$	46	50	—	%
Return Loss	IRL	—	-10	-7	dB

All published data at  $T_{CASE} = 25^\circ\text{C}$  unless otherwise indicated

**ESD:** Electrostatic discharge sensitive device—observe handling precautions!

## RF Characteristics

**Typical RF Performance** (not subject to production test, verified by design/characterization in Infineon test fixture)  
 $V_{DD} = 50\text{ V}$ ,  $I_{DQ} = 50\text{ mA}$ , Input signal ( $t_r = 7\text{ ns}$ ,  $t_f = 8\text{ ns}$ ),  $300\text{ }\mu\text{s}$  pulse width, 10% duty cycle, class AB test

Mode of Operation	$f$ (MHz)	IRL (dB)	P <sub>1dB</sub>			P <sub>3dB</sub>			Max P <sub>droop</sub> (pulse) dB @ 50 W	$t_r$ (ns) @ 50 W*	$t_f$ (ns) @ 50 W*
			Gain (dB)	Eff (%)	P <sub>OUT</sub> (W)	Gain (dB)	Eff (%)	P <sub>OUT</sub> (W)			
Pulsed RF	1200	-8	16	56	60	14	58	78	0.20	5	<2
Pulsed RF	1300	-10	16	57	60	14	58	78	0.20	5	<2
Pulsed RF	1400	-8	16	55	54	14	57	57	0.15	5	<2

\* Note =  $t_r$  and  $t_f$  are defined as  $\Delta$  between input and output rise and fall times

**Typical RF Performance** (not subject to production test, verified by design/characterization in Infineon test fixture)  
 $V_{DD} = 50\text{ V}$ ,  $I_{DQ} = 50\text{ mA}$ , 30 ms pulse width, 33% duty cycle, class AB test

Mode of Operation	$f$ (MHz)	P <sub>1dB</sub>			P <sub>3dB</sub>			P <sub>droop</sub> (pulse) dB @ 50 W
		Gain (dB)	Eff (%)	P <sub>OUT</sub> (W)	Gain (dB)	Eff (%)	P <sub>OUT</sub> (W)	
Pulsed RF	1200	16	57	57	14	59	75	0.3
Pulsed RF	1300	16	56	55	14	58	75	0.3
Pulsed RF	1400	16	49	50	14	50	55	0.2

## DC Characteristics

Characteristic	Conditions	Symbol	Min	Typ	Max	Unit
Drain-Source Breakdown Voltage	$V_{GS} = 0\text{ V}$ , $I_{DS} = 10\text{ mA}$	$V_{(BR)DSS}$	105	—	—	V
Drain Leakage Current	$V_{DS} = 50\text{ V}$ , $V_{GS} = 0\text{ V}$	$I_{DSS}$	—	—	1	$\mu\text{A}$
	$V_{DS} = 105\text{ V}$ , $V_{GS} = 0\text{ V}$	$I_{DSS}$	—	—	10	$\mu\text{A}$
On-State Resistance	$V_{GS} = 10\text{ V}$ , $V_{DS} = 0.1\text{ V}$	$R_{DS(on)}$	—	0.4	—	$\Omega$
Operating Gate Voltage	$V_{DS} = 50\text{ V}$ , $I_{DQ} = 50\text{ mA}$	$V_{GS}$	3.0	3.5	4.0	V
Gate Leakage Current	$V_{GS} = 10\text{ V}$ , $V_{DS} = 0\text{ V}$	$I_{GSS}$	—	—	1	$\mu\text{A}$

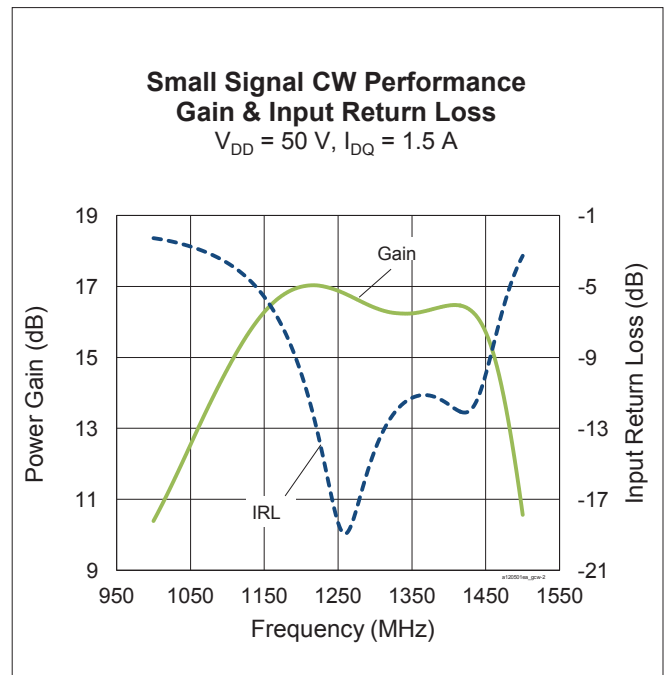
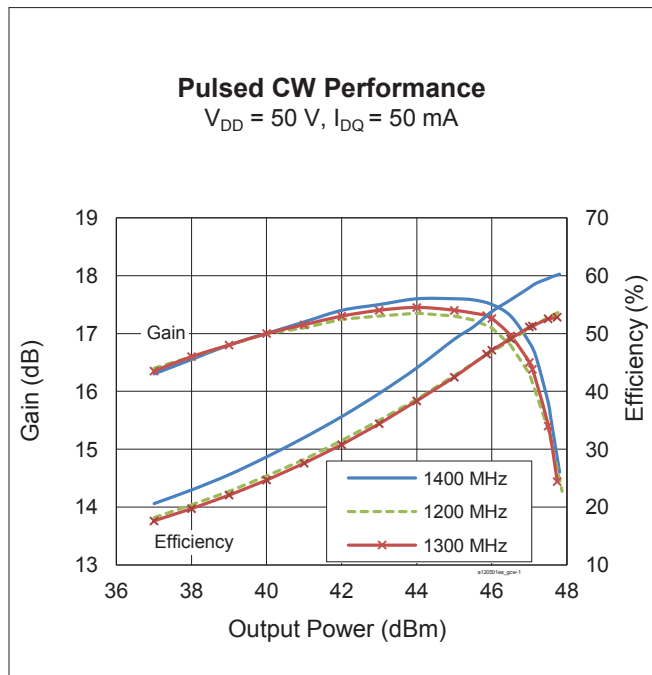
### Maximum Ratings

Parameter	Symbol	Value	Unit
Drain-Source Voltage	$V_{DSS}$	105	V
Gate-Source Voltage	$V_{GS}$	-6 to +12	V
Operating Voltage	$V_{DD}$	0 to +55	V
Junction Temperature	$T_J$	225	°C
Storage Temperature Range	$T_{STG}$	-65 to +150	°C
Thermal Resistance ( $T_{CASE} = 70^{\circ}C, 50 W CW$ )	$R_{\theta JC}$	1.37	°C/W

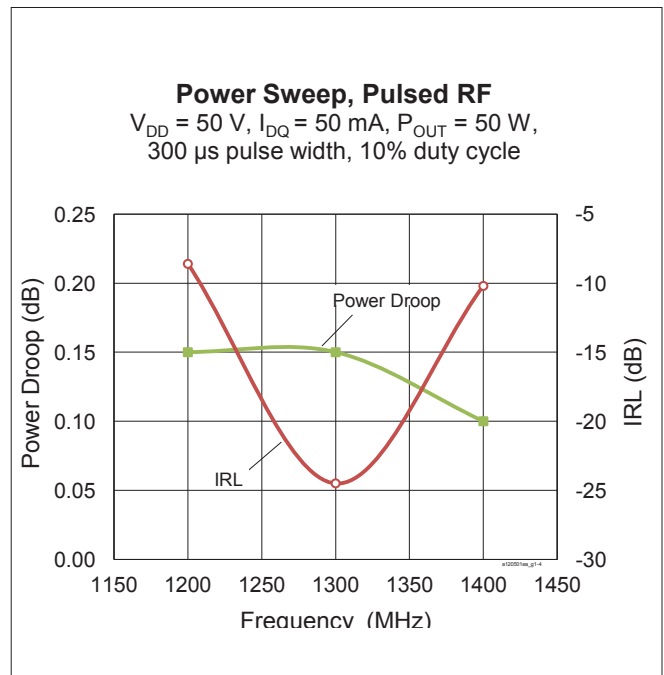
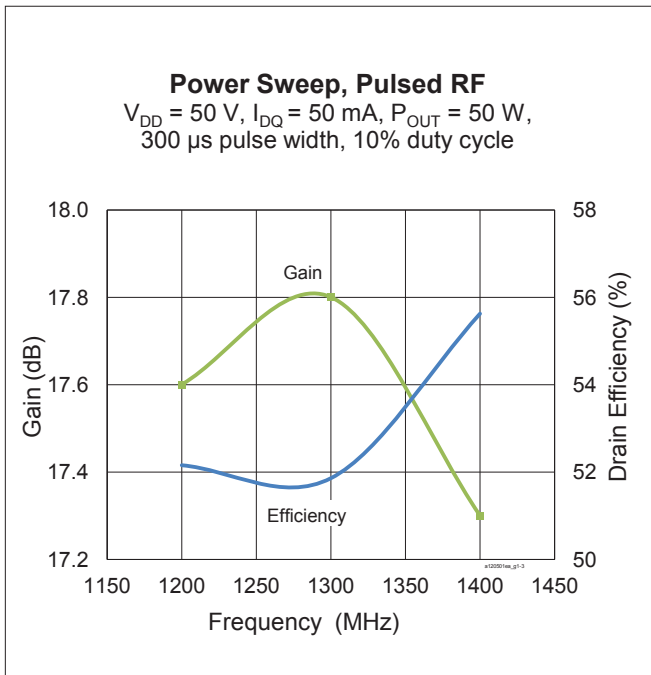
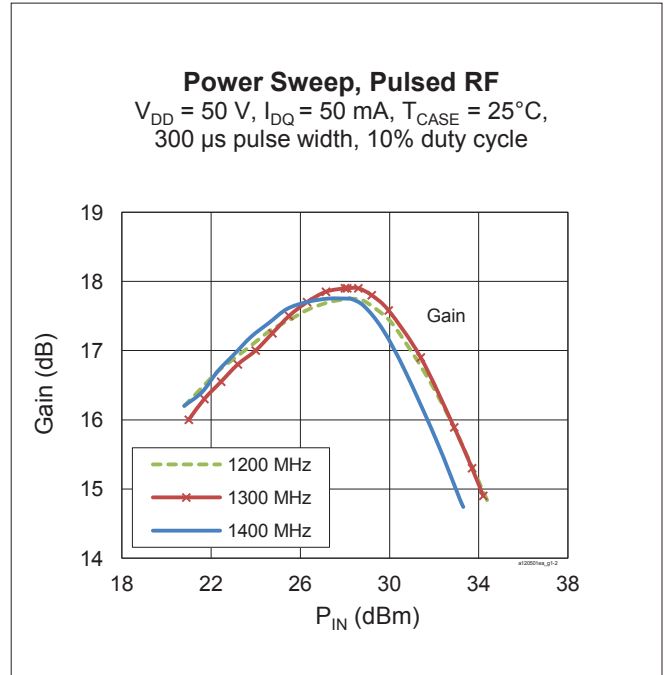
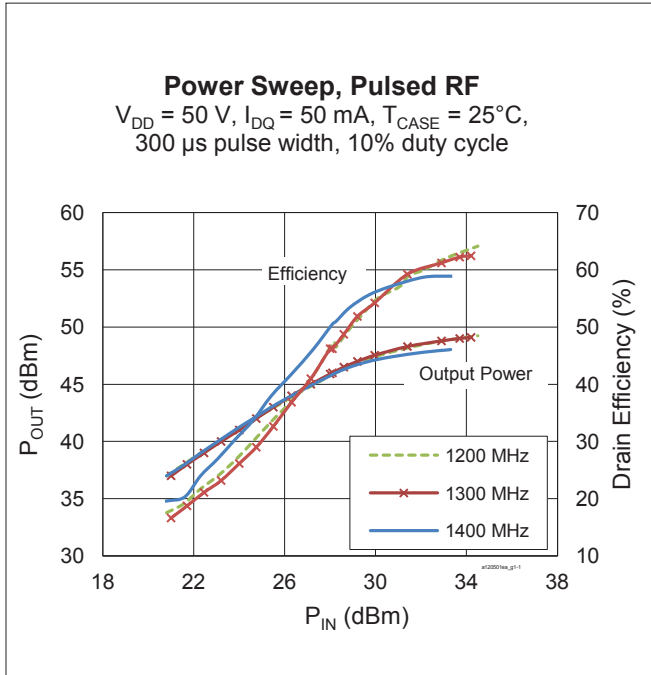
### Ordering Information

Type and Version	Order Code	Package Description	Shipping
PTVA120501EA V1 R0	PTVA120501EAV1R0XTMA1	H-36265-2, bolt-down	Tape & Reel, 50 pcs
PTVA120501EA V1 R2	PTVA120501EAV1R2XTMA1	H-36265-2, bolt-down	Tape & Reel, 250 pcs

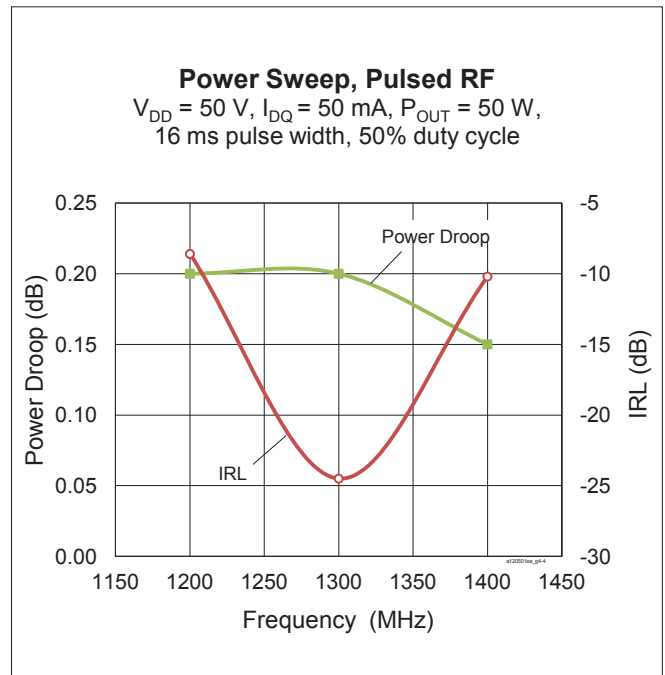
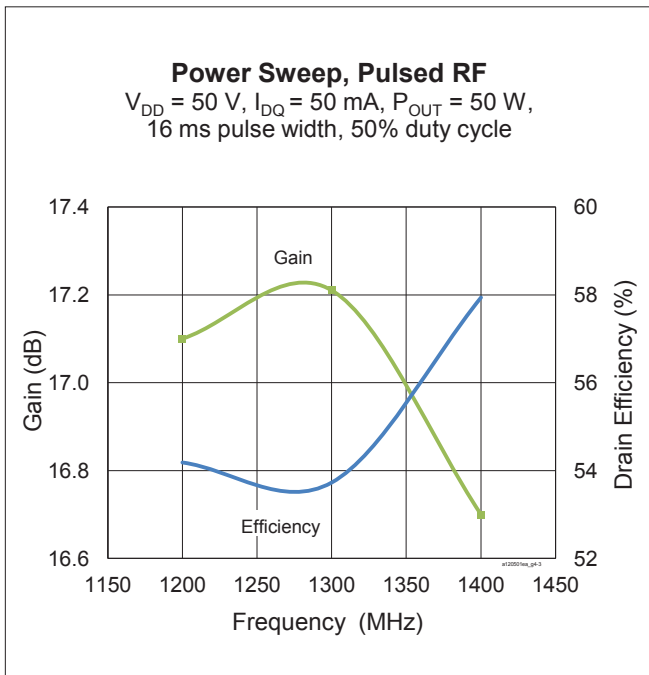
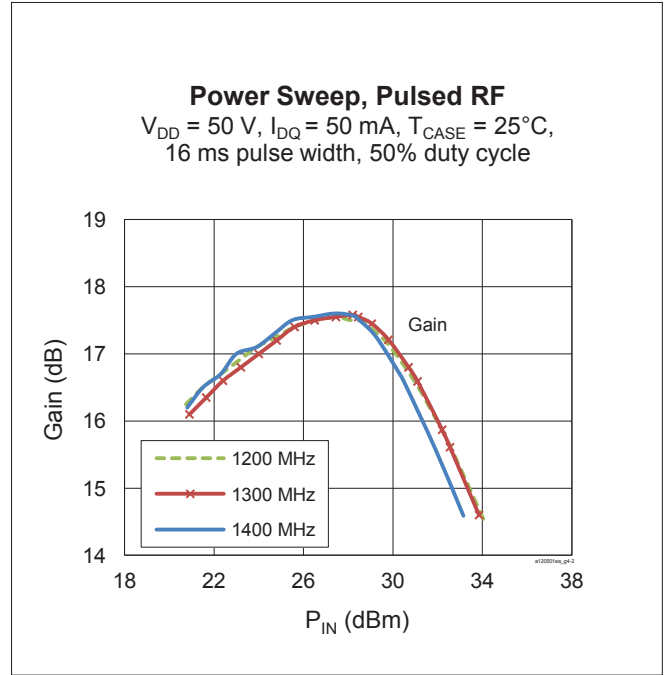
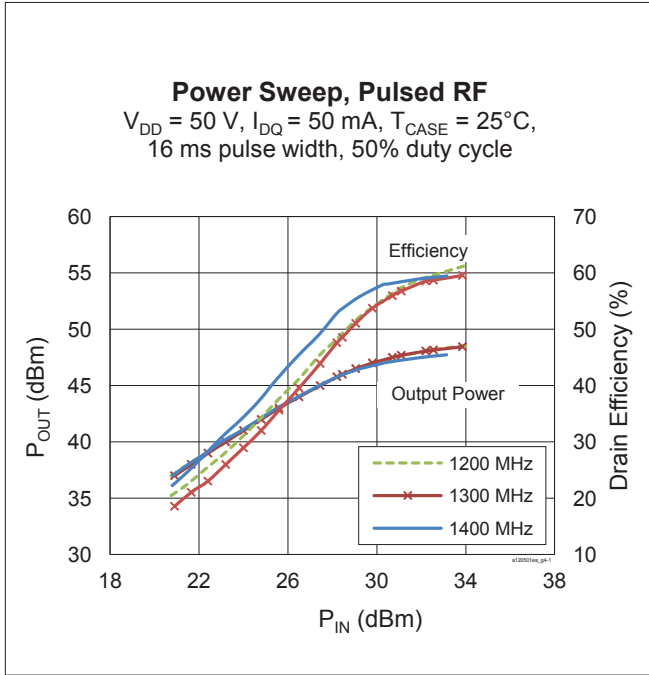
### Typical Performance (data taken in a production test fixture)



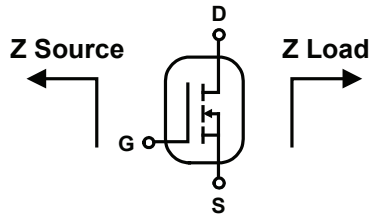
Typical Performance (cont.)



Typical Performance (cont.)



## Broadband Circuit Impedance



Freq [MHz]	Z Source $\Omega$		Z Load $\Omega$	
	R	jX	R	jX
1200	8.07	-2.13	3.66	4.97
1300	5.13	-0.95	3.90	4.56
1400	5.64	2.24	3.25	5.36

## Load Pull Performance

Load Pull at Max  $P_{OUT}$  Point – 16  $\mu$ s pulse width, 10% duty cycle, class AB,  $V_{DD} = 50$  V, 50 mA

Freq [MHz]	ZI [ $\Omega$ ]	$P_{IN}$ [dBm]	$P_{OUT}$ [dBm]	$P_{OUT}$ [W]	$P_G$ [dB]	PAE Eff [%]	$Z_{OUT}$ [ $\Omega$ ]
1200	3.04 – j2.16	30.68	47.30	53.70	16.62	45.56	3.19 – j1.55

Load Pull at Max  $G_T$  Point – 16  $\mu$ s pulse width, 10% duty cycle, class AB,  $V_{DD} = 50$  V, 50 mA

Freq [MHz]	ZI [ $\Omega$ ]	$P_{IN}$ [dBm]	$P_{OUT}$ [dBm]	$P_{OUT}$ [W]	$P_G$ [dB]	PAE Eff [%]	$Z_{OUT}$ [ $\Omega$ ]
1200	3.04 – j2.16	27.50	46.10	40.74	18.60	57.50	2.88 – j4.11

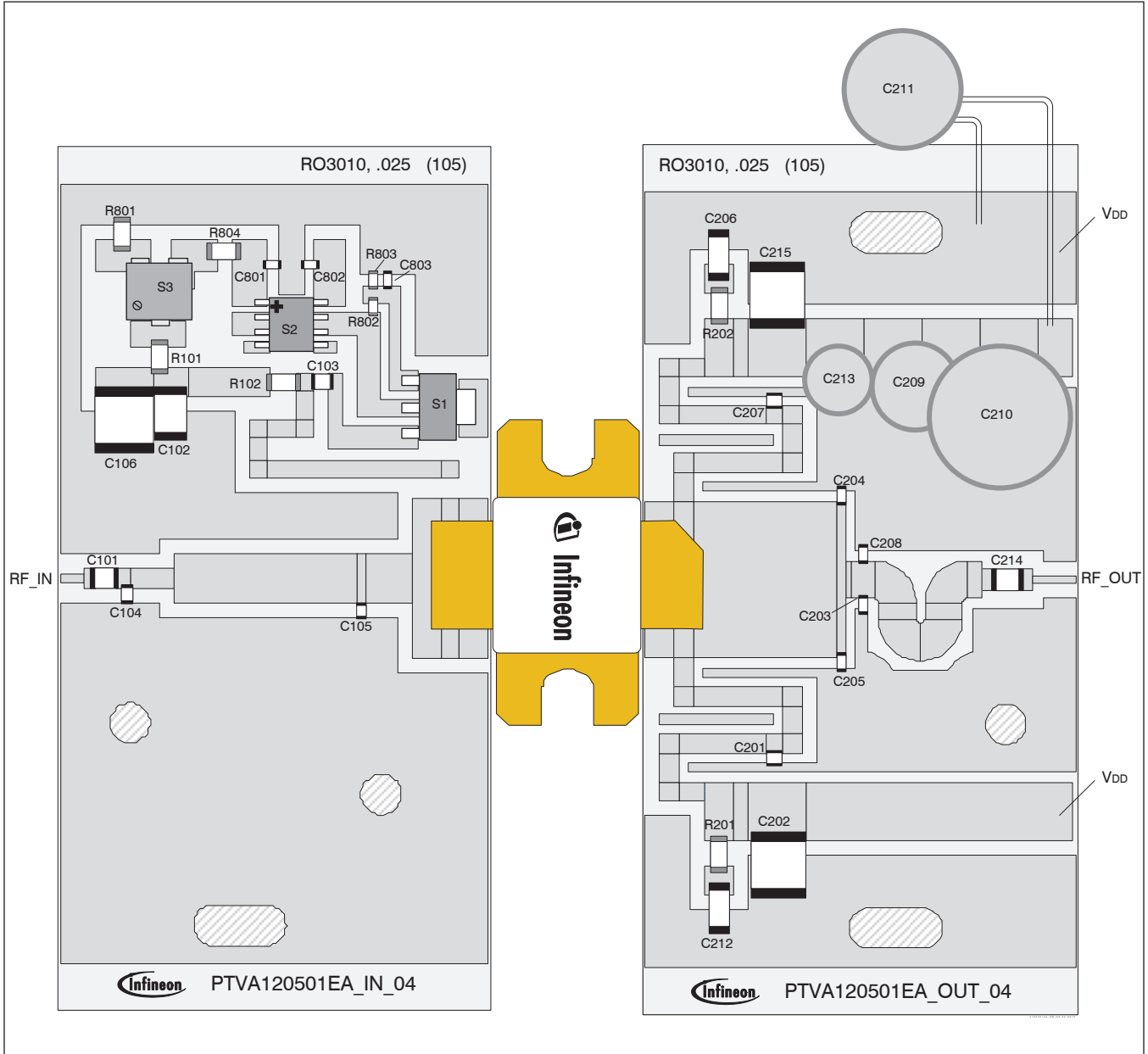
Load Pull at Max Efficiency Point – 16  $\mu$ s pulse width, 10% duty cycle, class AB,  $V_{DD} = 50$  V, 50 mA

Freq [MHz]	ZI [ $\Omega$ ]	$P_{IN}$ [dBm]	$P_{OUT}$ [dBm]	$P_{OUT}$ [W]	$P_G$ [dB]	PAE Eff [%]	$Z_{OUT}$ [ $\Omega$ ]
1200	3.04 – j2.16	27.55	46.15	41.21	18.60	57.20	2.88 – j4.06

Z Optimum – 16  $\mu$ s pulse width, 10% duty cycle, class AB,  $V_{DD} = 50$  V, 50 mA

Freq [MHz]	ZI [ $\Omega$ ]	$P_{IN}$ [dBm]	$P_{OUT}$ [dBm]	$P_{OUT}$ [W]	$P_G$ [dB]	PAE Eff [%]	$Z_{OUT}$ [ $\Omega$ ]
1200	3.04 – j2.16	28.70	46.57	45.39	17.87	50.46	2.92 – j3.12

Reference Circuit , 1200 – 1400 MHz



Reference circuit assembly diagram (not to scale)

**Reference Circuit** (cont.)

**Reference Circuit Assembly**

DUT	PTVA120501EA
Test Fixture Part No.	LTN/PTVA120501EA V1
PCB	Rogers 6006, 0.635 mm [0.025"] thick, 2 oz. copper, $\epsilon_r = 6.15$ , $f = 1200 - 1400$ MHz

**Components Information**

Component	Description	Suggested Manufacturer	P/N
<b>Input</b>			
C101	Capacitor, 39 pF	ATC	ATC100B390KW500XB
C102	Capacitor, 1 $\mu$ F	TDK Corporation	C4532X7R2A105M230KA
C103	Capacitor, 33 pF	ATC	ATC100A330JW150XB
C104	Capacitor, 2.7 pF	ATC	ATC800A2R7BT
C105	Capacitor, 10 pF	ATC	ATC800A100JT
C106	Capacitor, 10 $\mu$ F	TDK Corporation	C5750X5R1H106K230KA
C801, C802, C803	Capacitor, 1000 pF	Panasonic Electronic Components	ECJ-1VB1H102K
R101	Resistor, 1000 $\Omega$	Panasonic Electronic Components	ERJ-8GEYJ102V
R102	Resistor, 10 $\Omega$	Panasonic Electronic Components	ERJ-8GEYJ100V
R801	Resistor, 2000 $\Omega$	Panasonic Electronic Components	ERJ-8GEYJ202V
R802	Resistor, 1200 $\Omega$	Panasonic Electronic Components	ERJ-3GEYJ122V
R803	Resistor, 1300 $\Omega$	Panasonic Electronic Components	ERJ-3GEYJ132V
R804	Resistor, 100 $\Omega$	Panasonic Electronic Components	ERJ-8GEYJ100V
S1	Transistor	Infineon Technologies	BCP56
S2	Voltage Regulator	Texas Instruments	LM78L05ACM
S3	Potentiometer, 2k $\Omega$	Bourns Inc.	3224W-1-202E
<b>Output</b>			
C201, C207	Capacitor, 33 pF	ATC	ATC100A330JW150XB
C202, C215	Capacitor, 10 $\mu$ F	TDK Corporation	C5750X5R1H106K230KA
C203, C208	Capacitor, 3.9 pF	ATC	ATC800A3R9BT
C204, C205	Capacitor, 6.8 pF	ATC	ATC800A6R8BT
C206, C212	Capacitor, 1 $\mu$ F	TDK Corporation	C4532X7R2A105M230KA
C209	Capacitor, 22 $\mu$ F	Cornell Dubilier Electronics (CDE)	SEK220M100ST
C210	Capacitor, 100 $\mu$ F	Cornell Dubilier Electronics (CDE)	SK101M100ST
C211	Capacitor, 6800 $\mu$ F	Cornell Dubilier Electronics (CDE)	ECO-S2AP682EA
C213	Capacitor, 10 $\mu$ F	Cornell Dubilier Electronics (CDE)	SEK100M100ST
C214	Capacitor, 39 pF	ATC	ATC100B390KW500XB
R201, R202	Resistor, 5600 $\Omega$	Panasonic Electronic Components	ERJ-8RQJ5R6V



### Package Outline Specifications



Find the latest and most complete information about products and packaging at the Infineon Internet page <http://www.infineon.com/rfpower>

## Revision History

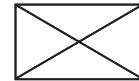
Revision	Date	Data Sheet Type	Page	Subjects (major changes since last revision)
01	2013-05-29	Advance	All	Data Sheet reflects advance specification for product development
02	2013-09-24	Production	All	Data Sheet reflects released product specification
02.1	2016-05-26	Production	3	Updated ordering information
02.2	2017-02-07	Production	3	Updated operating voltage and junction temperature

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